

DESCRIPTION

M63806P/FP/KP are eight-circuit Single transistor arrays. The circuits are made of NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

FEATURES

- Three package configurations (P, FP, and KP)
- Medium breakdown voltage ($BV_{CEO} \geq 35V$)
- Synchronizing current ($I_{C(max)} = 300mA$)
- Low output saturation voltage
- Wide operating temperature range ($T_a = -40$ to $+85^\circ C$)

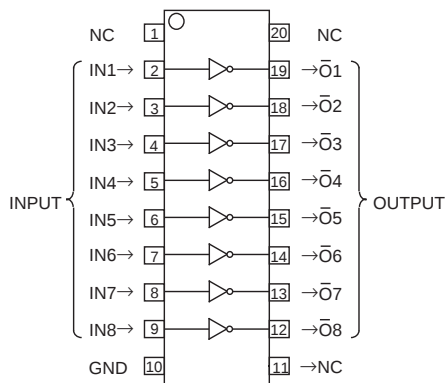
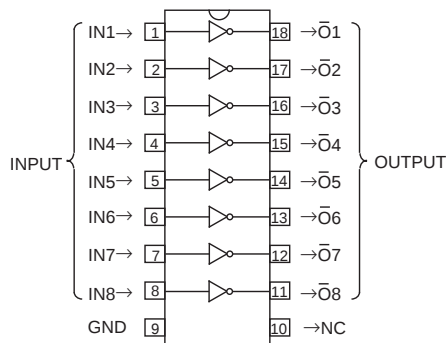
APPLICATION

Driving of digit drives of indication elements (LEDs and lamps) with small signals

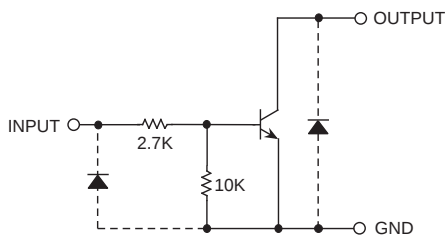
FUNCTION

The M63806P/FP/KP each have eight circuits consisting of NPN transistor. The transistor emitters are all connected to the GND pin. The transistors allow synchronous flow of 300mA collector current. A maximum of 35V voltage can be applied between the collector and emitter.

PIN CONFIGURATION



CIRCUIT DIAGRAM



The eight circuits share the GND.

The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit: Ω

POWEREX

M63806P/FP/KP

8-UNIT 300mA TRANSISTOR ARRAY

ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted, Ta = -40 ~ +85°C)

Symbol	Parameter	Conditions		Ratings	Unit
V _{CE0}	Collector-emitter voltage	Output, H		−0.5 ~ +35	V
I _C	Collector current	Current per circuit output, L		300	mA
V _I	Input voltage			−0.5 ~ +35	V
P _d	Power dissipation	Ta = 25°C, when mounted on board	M63806P	1.79	W
			M63806FP	1.10	
			M63806KP	0.68	
T _{opr}	Operating temperature			−40 ~ +85	°C
T _{stg}	Storage temperature			−55 ~ +125	°C

RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted, Ta = -40 ~ +85°C)

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
V _O	Output voltage		0	—	35	V
I _C	Collector current (Current per 1 circuit when 8 circuits are coming on simultaneously)	M63806P Duty Cycle no more than 50%	0	—	250	mA
			0	—	170	
		M63806FP Duty Cycle no more than 30%	0	—	250	
			0	—	130	
		M63806KP Duty Cycle no more than 12%	0	—	250	
			0	—	100	
V _{IN}	Input voltage		0	—	20	V

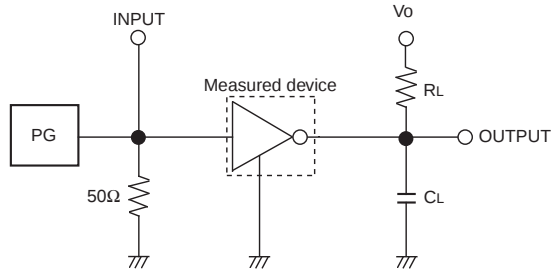
ELECTRICAL CHARACTERISTICS (Unless otherwise noted, Ta = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
V (BR) CEO	Collector-emitter breakdown voltage	I _{CEO} = 10μA	35	—	—	V
V _{CE(sat)}	Collector-emitter saturation voltage	I _{IN} = 1mA, I _C = 10mA	—	—	0.2	V
		I _{IN} = 2mA, I _C = 150mA	—	—	0.8	
V _{IN(on)}	"On" input voltage	I _{IN} = 1mA, I _C = 10mA	2.4	3.5	4.2	V
h _{FE}	DC amplification factor	V _{CE} = 10V, I _C = 10mA	50	—	—	—

SWITCHING CHARACTERISTICS (Unless otherwise noted, Ta = 25°C)

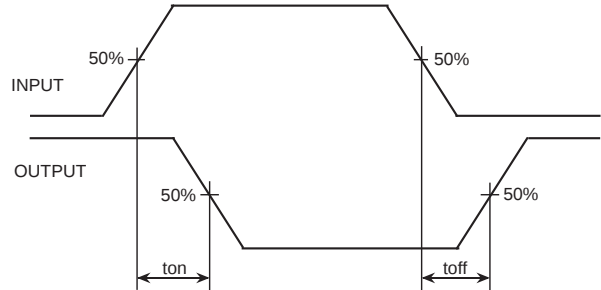
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
t _{on}	Turn-on time	C _L = 15pF (note 1)	—	125	—	ns
t _{off}	Turn-off time		—	250	—	ns

NOTE 1 TEST CIRCUIT



- (1) Pulse generator (PG) characteristics : PRR = 1kHz, $t_w = 10\mu s$, $t_r = 6ns$, $t_f = 6ns$, $Z_o = 50\Omega$, $V_{IH} = 3V$
- (2) Input-output conditions : $R_L = 220\Omega$, $V_o = 35V$
- (3) Electrostatic capacity C_L includes floating capacitance at connections and input capacitance at probes

TIMING DIAGRAM



TYPICAL CHARACTERISTICS

